

EECS 16B

Designing Information Devices and Systems II
Lecture 9

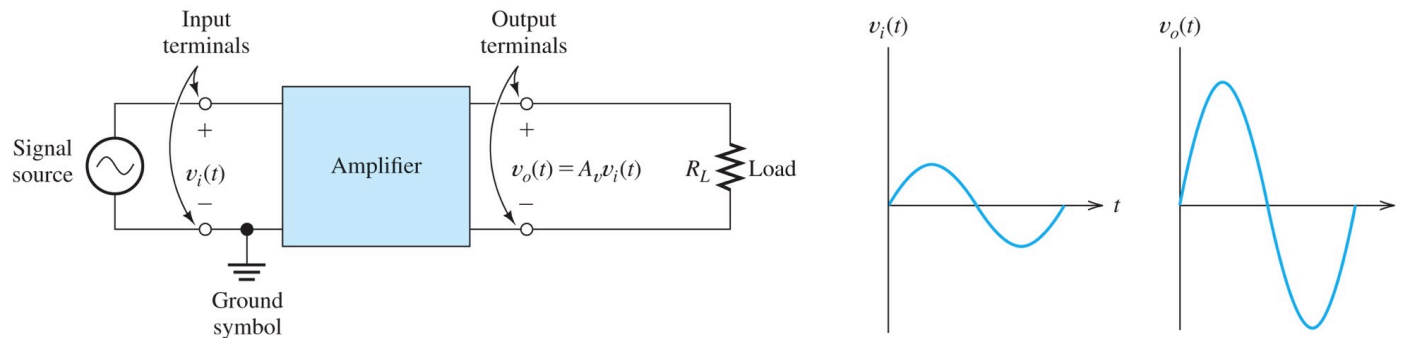
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Devices

- Outline
 - Amplifiers and Devices
- Reading-slides

Active Devices



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- Active devices are made of semiconductors
- Semi-conductors are materials whose resistance is in between a metal and insulator

Half

- More interestingly, one is able to change the resistance of the semiconductor materials by using external control such as voltage or current

Semiconductors

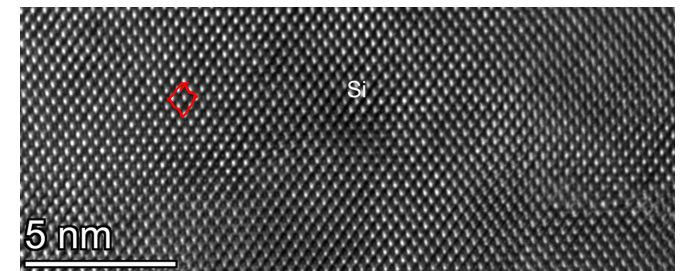
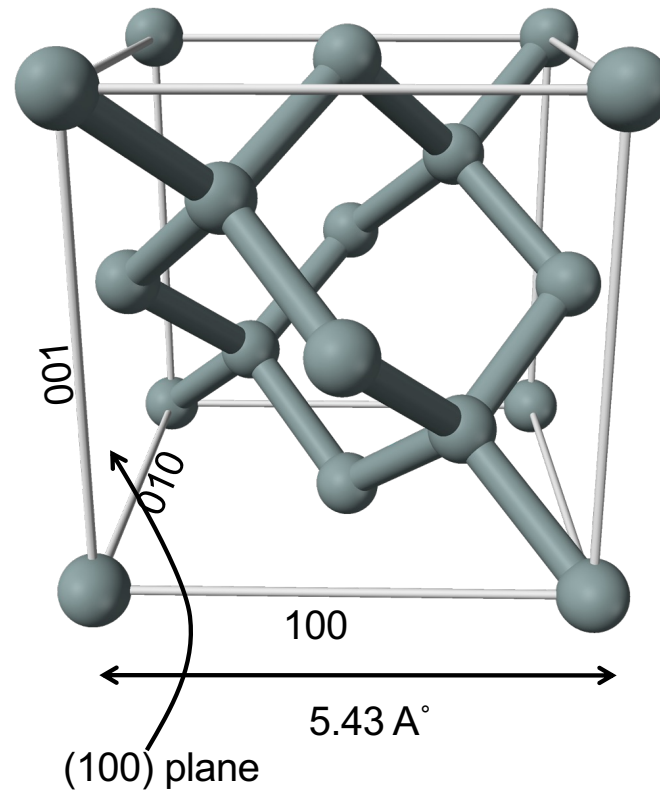
- Semiconductors are **usually** made of group IV elements- atoms that contain, on average, four valence electrons
- Most Common semiconductor used in electronic devices is **Silicon**

Periodic Table of the Elements

1	IA	1	H	IIA	2	He	0																														
2	3	Li	4	Be	5	B	6	C	7	N	8	O	9	F	10	Ne																					
3	11	Na	12	Mg	13	Al	14	Si	15	P	16	S	17	Cl	18	Ar																					
4	19	K	20	Ca	21	Sc	22	Ti	23	V	24	Cr	25	Mn	26	Fe	27	Co	28	Ni	29	Cu	30	Zn	31	Ga	32	Ge	33	As	34	Se	35	Br	36	Kr	
5	37	Rb	38	Sr	39	Y	40	Zr	41	Nb	42	Mo	43	Tc	44	Ru	45	Rh	46	Pd	47	Ag	48	Cd	49	In	50	Sn	51	Sb	52	Te	53	I	54	Xe	
6	55	Cs	56	Ba	57	*La	72	Hf	73	Ta	74	W	75	Re	76	Os	77	Ir	78	Pt	79	Au	80	Hg	81	Tl	82	Pb	83	Bi	84	Po	85	At	86	Rn	
7	87	Fr	88	Ra	89	+Ac	104	Rf	105	Ha	106	Sg	107	Ns	108	Hs	109	Mt	110	111	112	113															

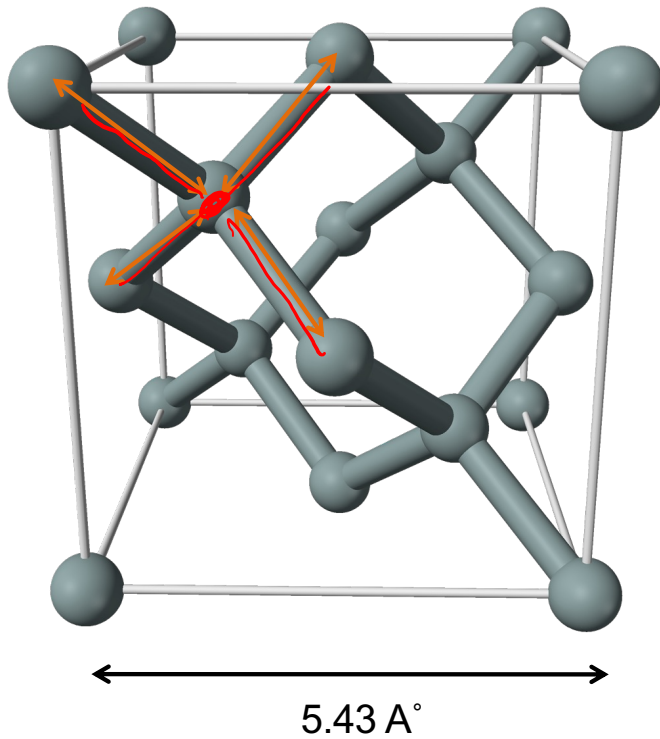
Crystal Structure of Si

Often known as the diamond lattice

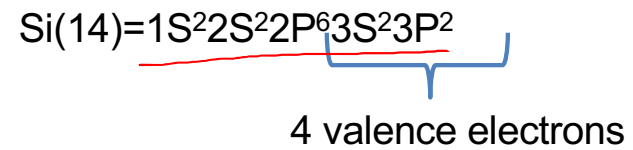


Transmission Electron Microscopy
Image of Si taken at Lawrence
Berkeley National Laboratory

Crystal Structure of Si



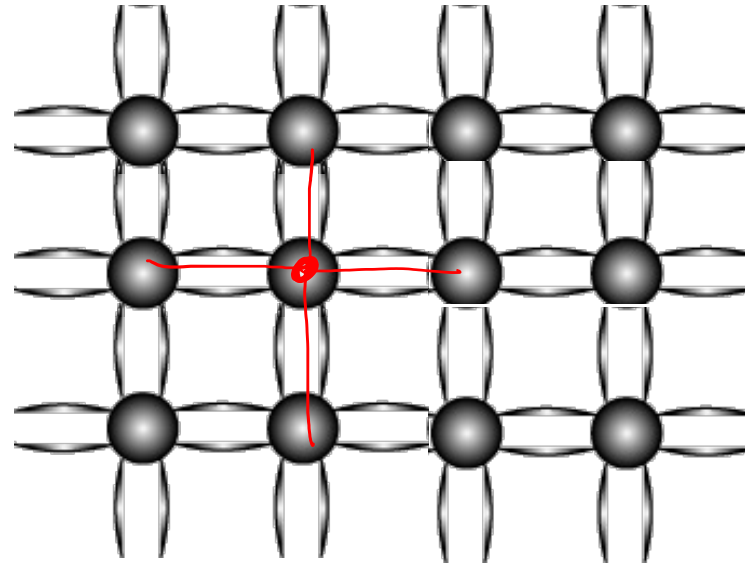
Each atom has 4 nearest neighbors



Each atom shares 2 electrons with 4 nearest neighbors to form a covalent bond

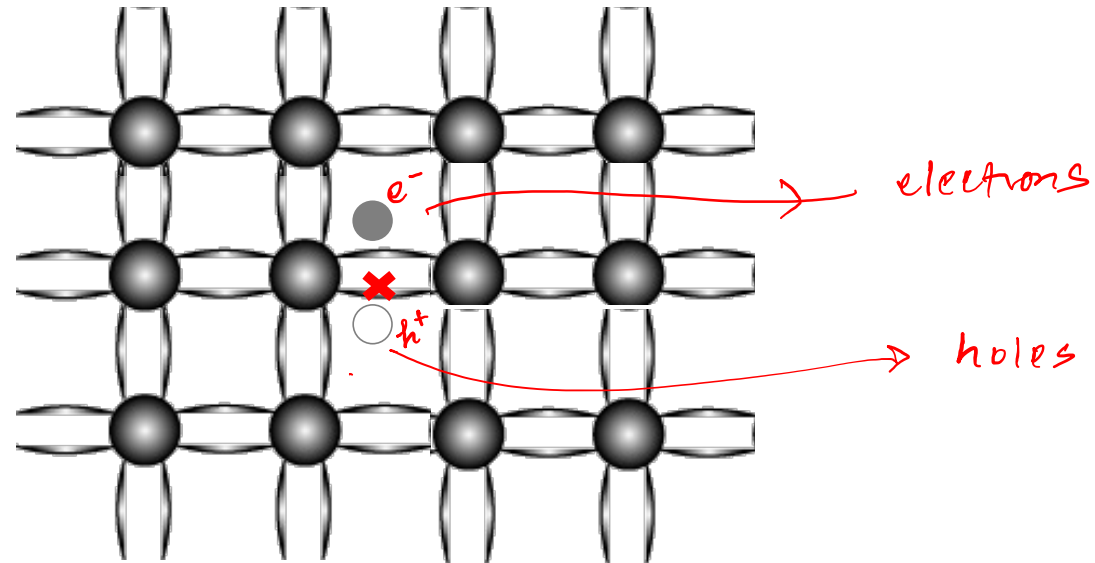
The Bond Model

Each atom shares 2 electrons with 4 nearest neighbors to form a covalent bond



At $T=0\text{K}$, all bonds are satisfied, there are no **free** carriers, no current flows,
→ looks like an insulator

Intrinsic Si: The Bond Model: Electrons

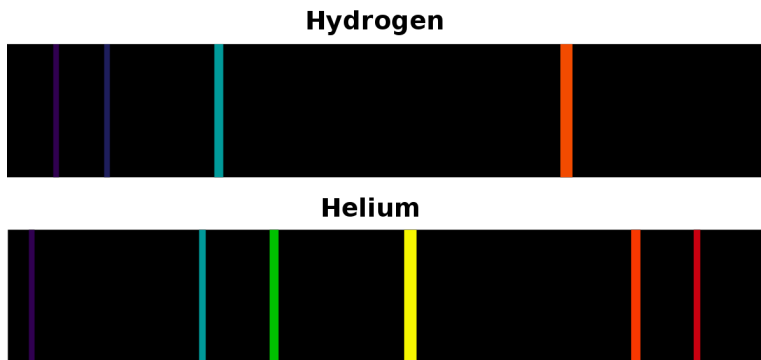


At finite temperature, an electron may gain enough energy to break the covalent bond, become **free** and move around.

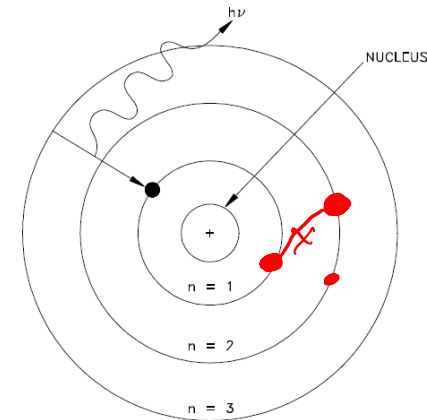
Energy Band Model

Electrons around nucleus

It was known from John Herschel's experiment in (1826) that heated gas emits a unique combination of colors

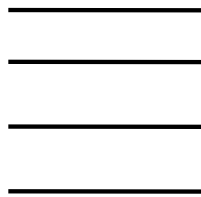


- In 1913 Niels Bohr proposed an atomic model that assumes electrons are orbiting around a positively charged nucleus in **specific shells**

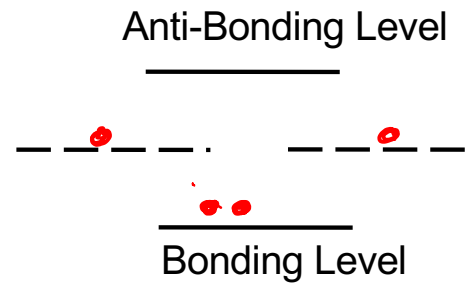


- When heated electrons can absorb the energy and go from shell 1 to 2. When cooling down, it comes down to 1, **emitting** the specific energy difference between 2 and 1 giving a specific color of light.

Energy Levels and Formation of a Molecule



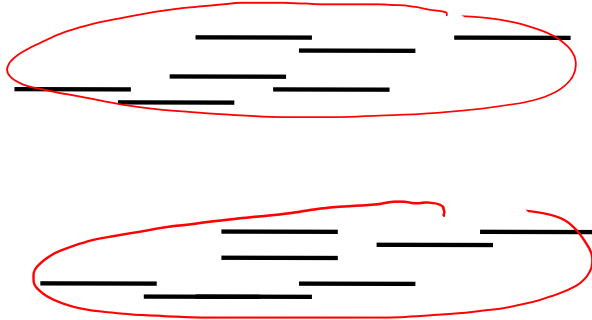
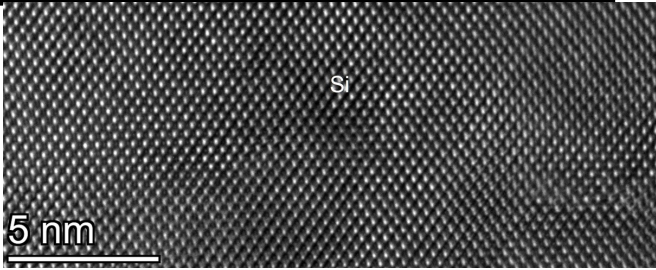
Discrete energy levels in an atom



When energy levels of two atoms interact, they create one bonding and one anti-bonding level

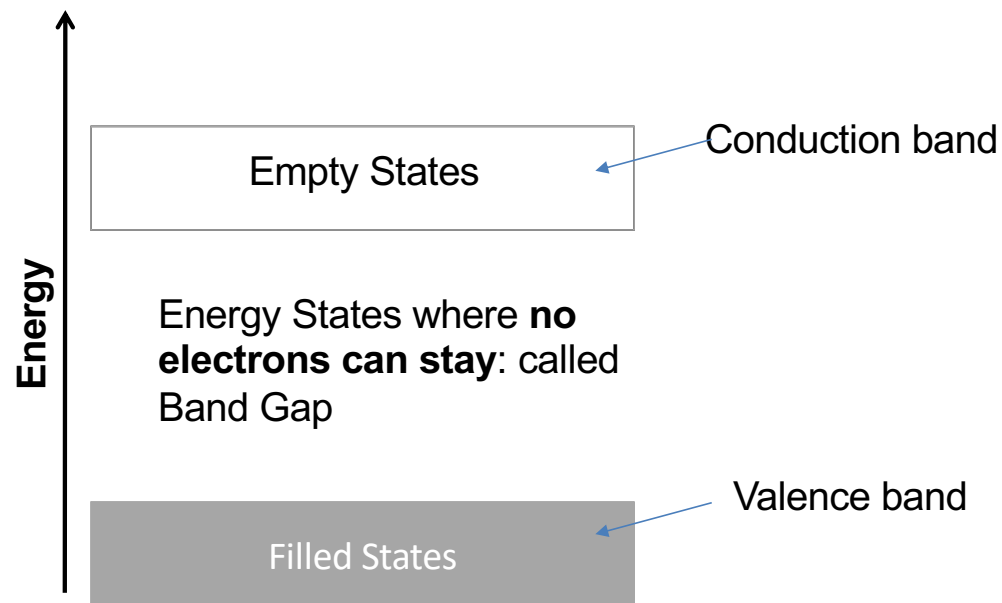
Energy Bands

In a solid as many atoms are brought close to each other they create many many bonding and anti-bonding levels

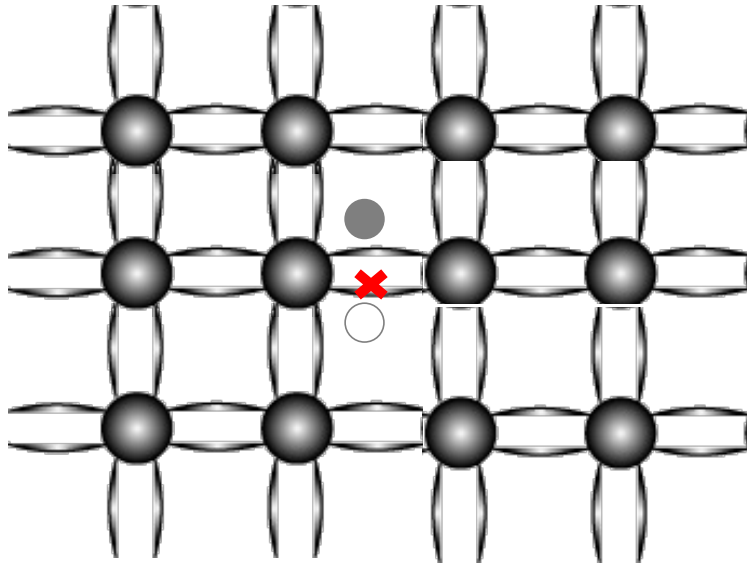
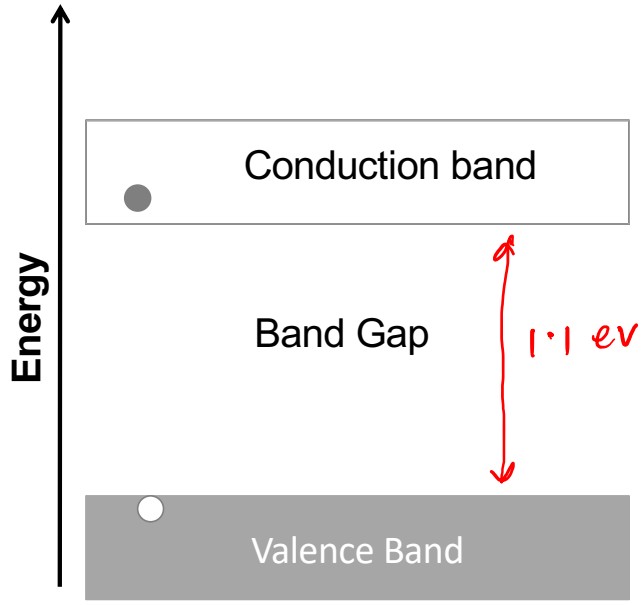


Energy Bands

Energy Bands

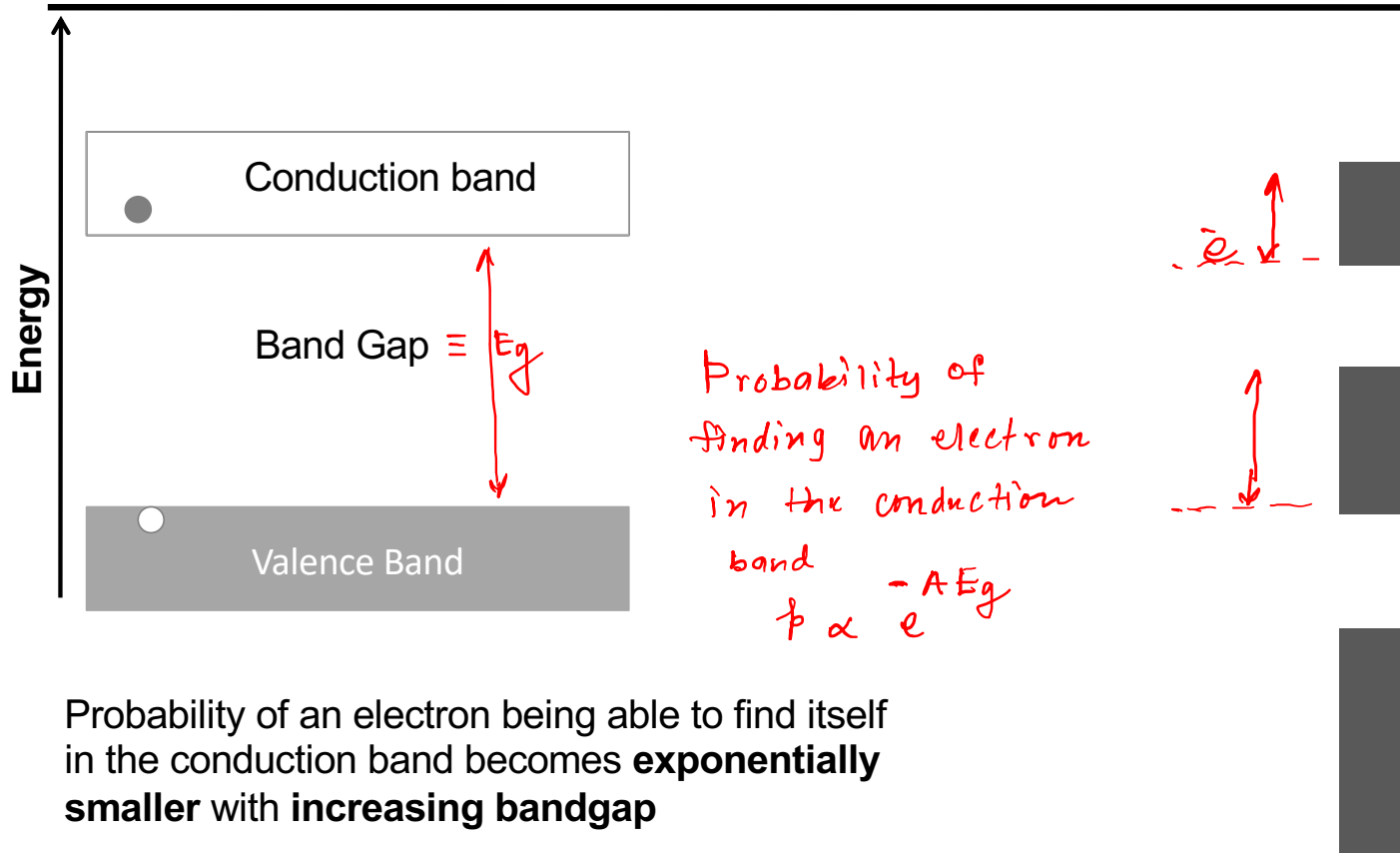


Energy Bands



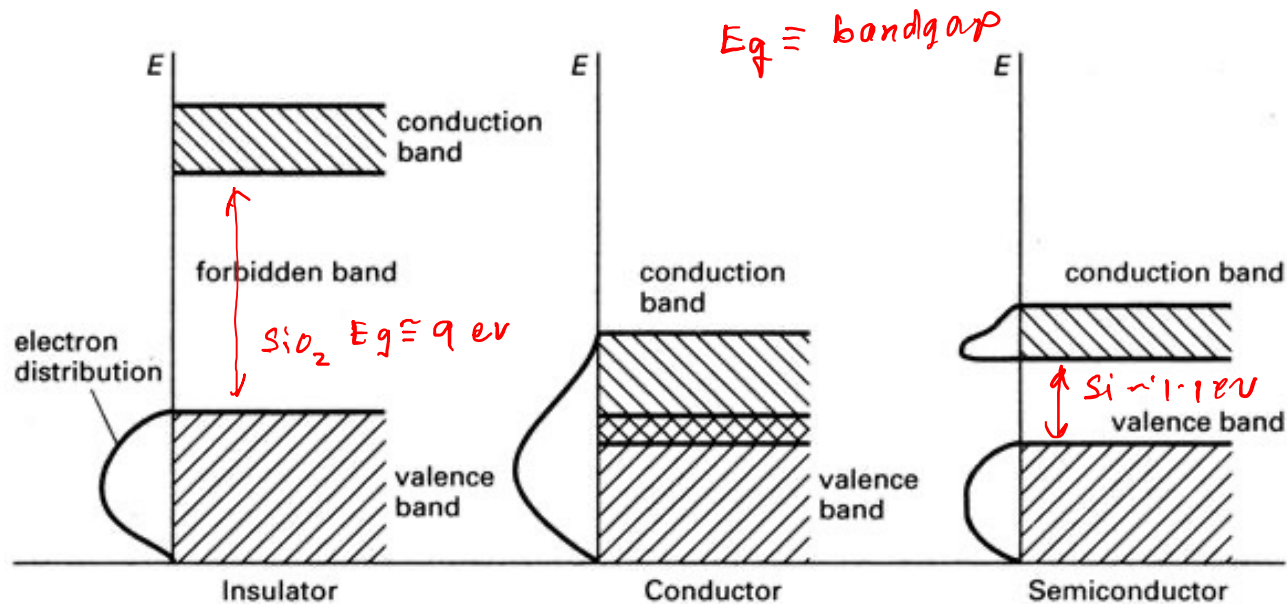
$k_B T \sim 26 \text{ meV}$
→ Boltzmann constant

Probability of an electron being free



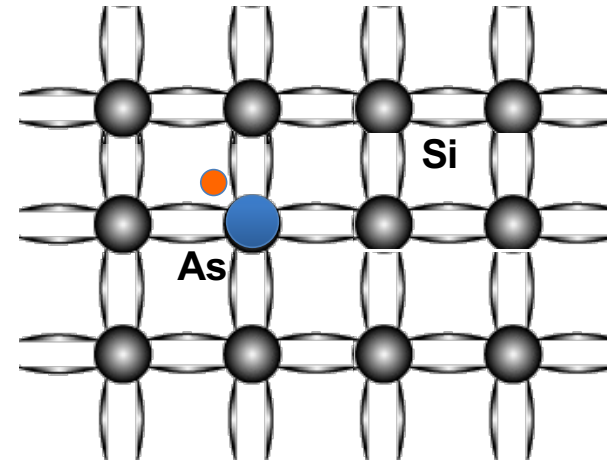
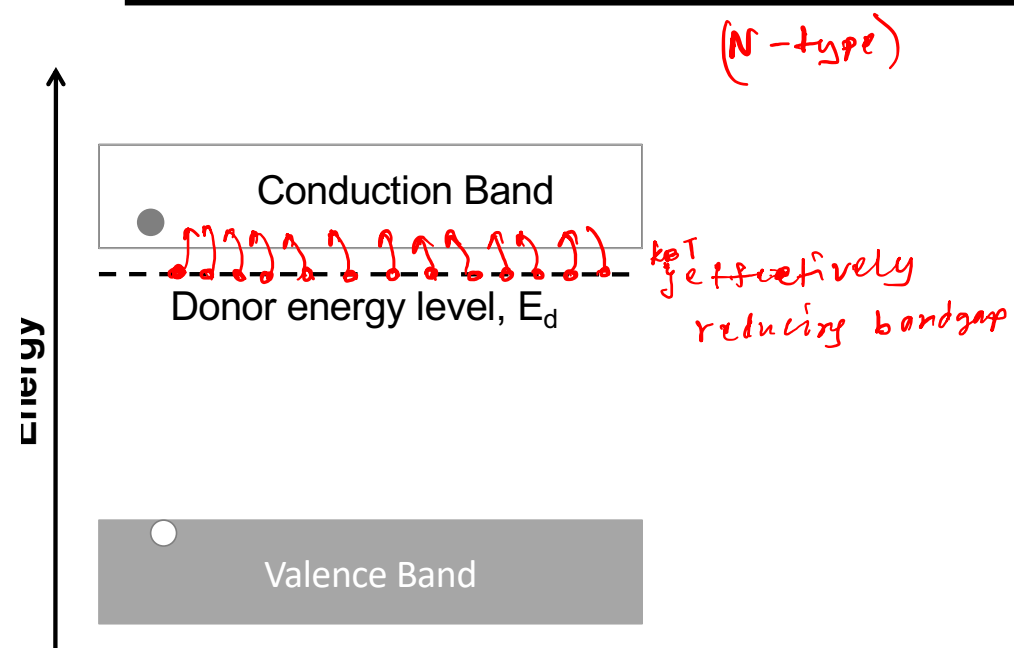
Probability of an electron being able to find itself in the conduction band becomes **exponentially smaller** with **increasing bandgap**

Semiconductors, Insulators and Conductors



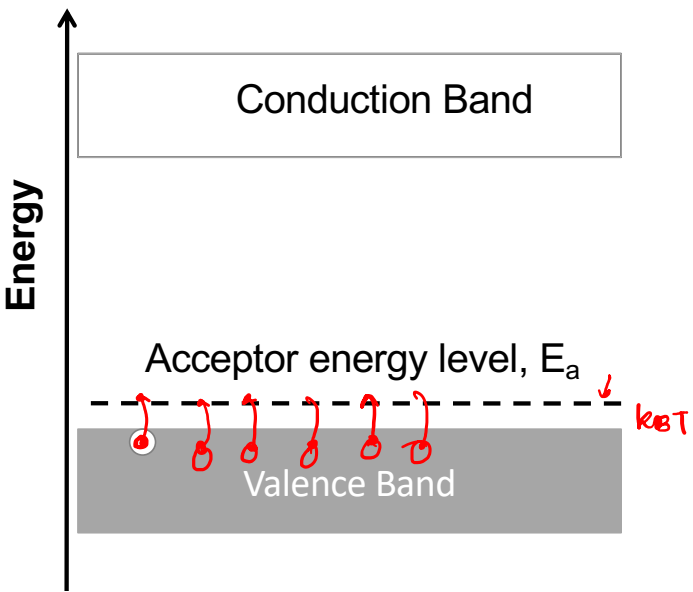
- ✓ Conductors have half filled bands
- ✓ Semiconductors have lower energy gap compared to insulators and can be doped

Doping

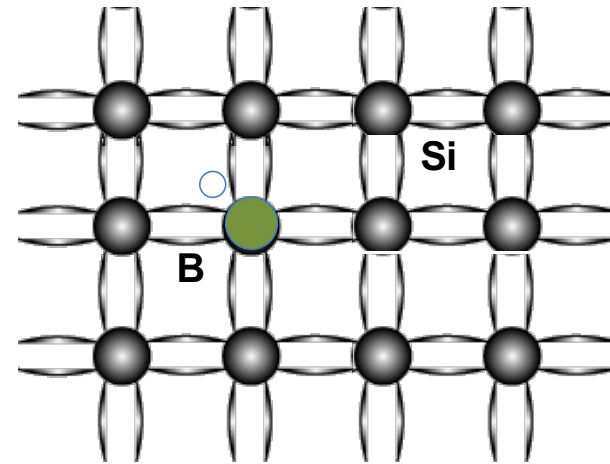


	III	IV	V	
	Boron (B)	Carbon (C)		
...	Aluminum (Al)	Silicon (Si)	Phosphorous (P)	...
	Galium (Al)	Germanium (Ge)	Arsenic (As)	
		⋮		

Doping

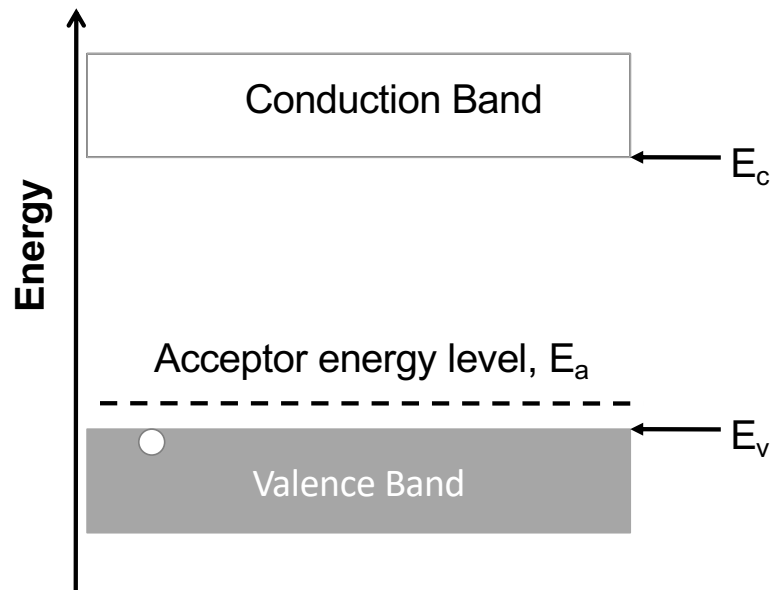


P-type doping



	III	IV	V	
	Boron (B)	Carbon (C)		
...	Aluminum (Al)	Silicon (Si)	Phosphorous (P)	...
	Galium (Al)	Germanium (Ge)	Arsenic (As)	
		...		

A convention about energy bands

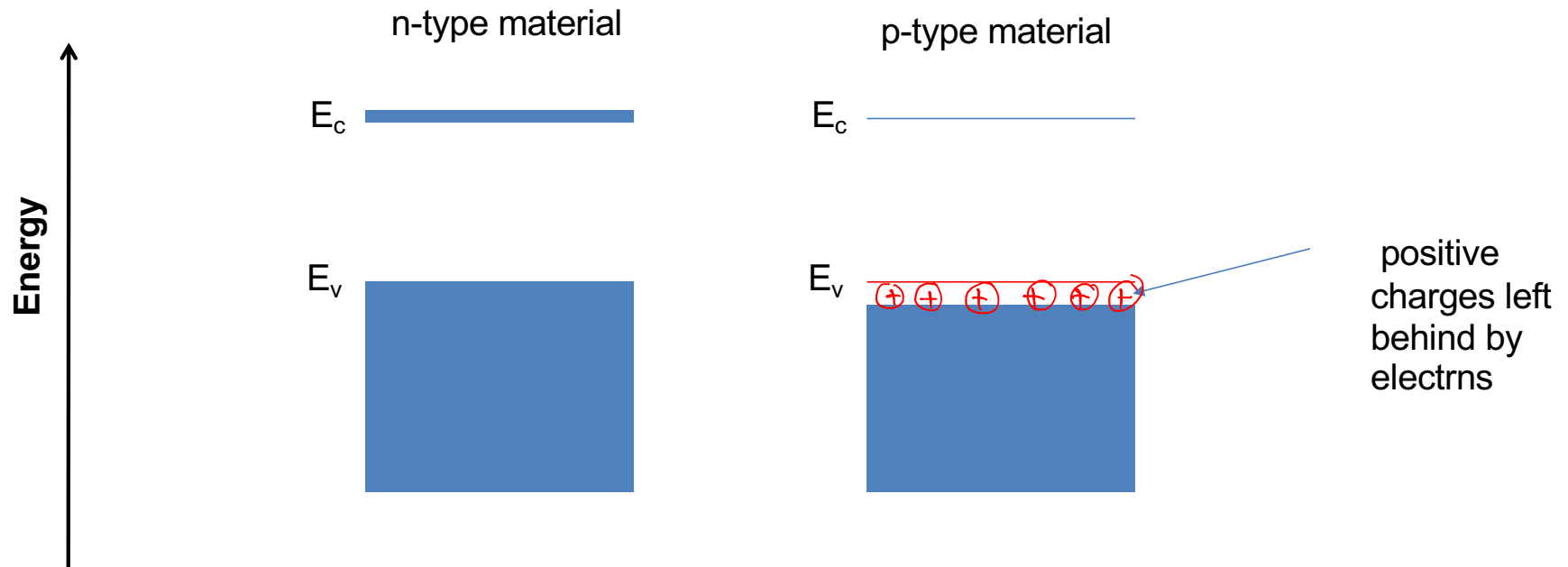


E_c —————

E_v —————

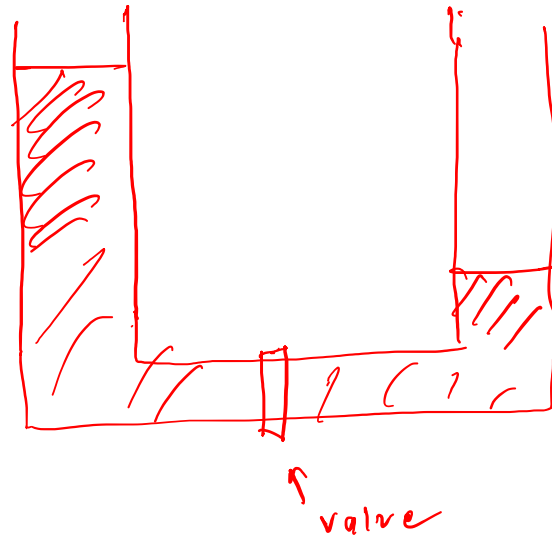
Only the edge of the bands are shown where the difference between the two edges is the bandgap

N and P type Materials, Junctions and Devices



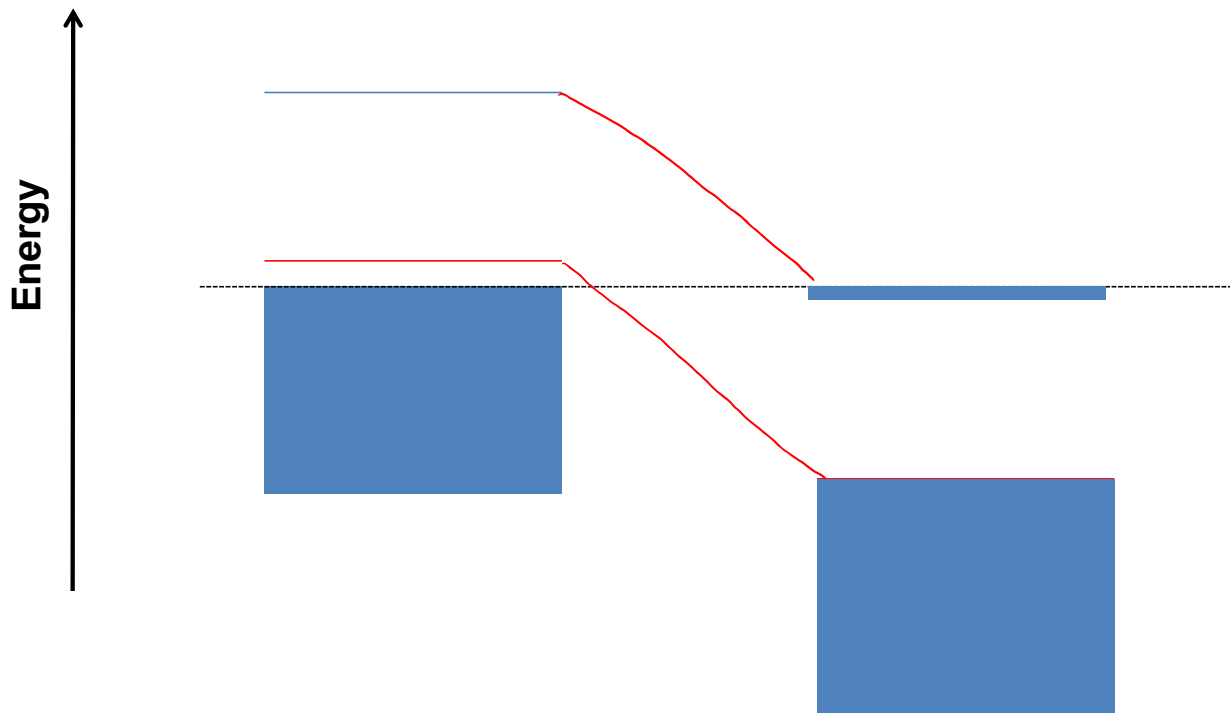
*Blue color indicates electrons

Combining N and P materials

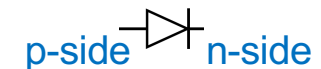


N and P type Materials, Junctions and Devices

Qualitative Picture of a Junction Formation



- When a n and p are put together, they form a p-n junction diode
Symbol:

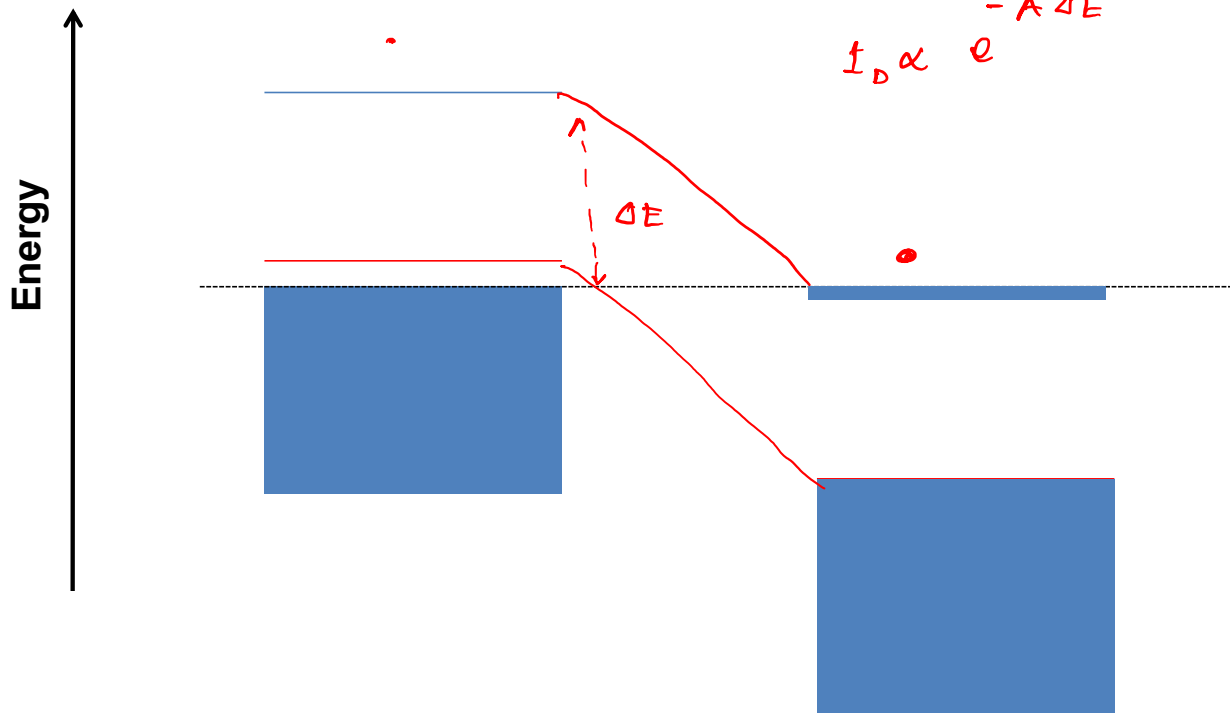


- Electron densities align in energy so that there is no difference in concentration
- Technically what aligns is the energy level where probability of finding an electron is $\frac{1}{2}$ → to be discussed in more details in EE130

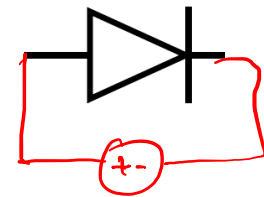
What does a voltage do?

$$u = qv \\ = -eV$$

Qualitative Picture of a Junction Formation

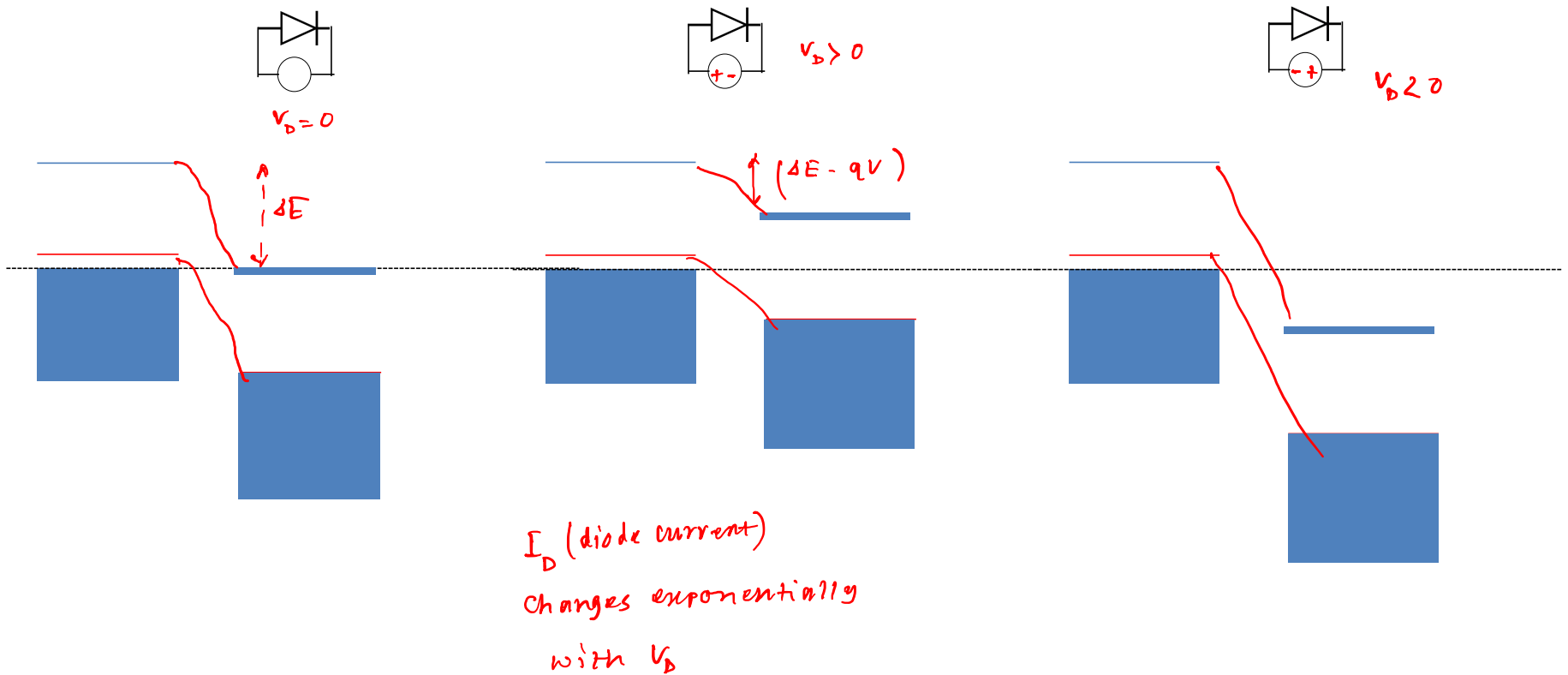


p-side n-side

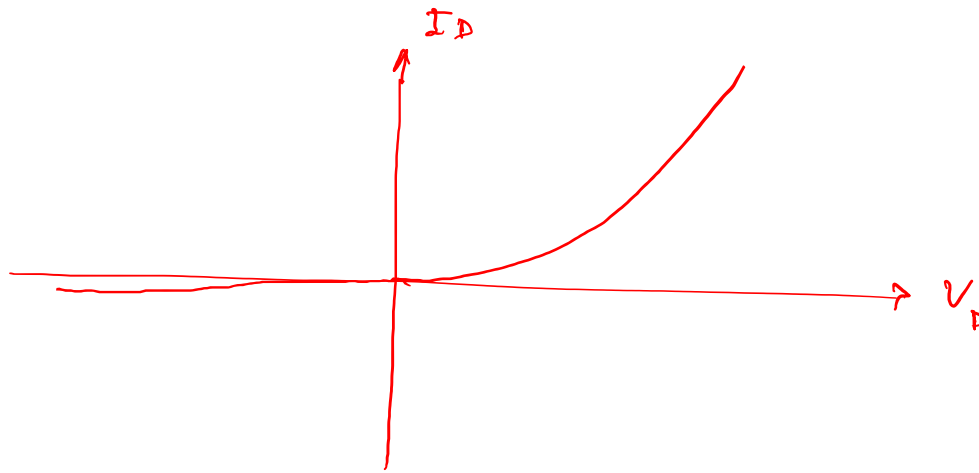


Negative terminal of a battery brings electrons and thereby **increases energy**.

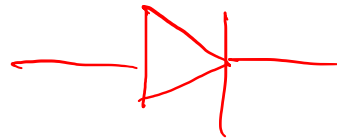
N and P type Materials, Junctions and Devices



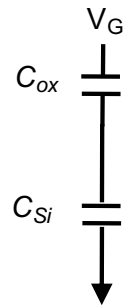
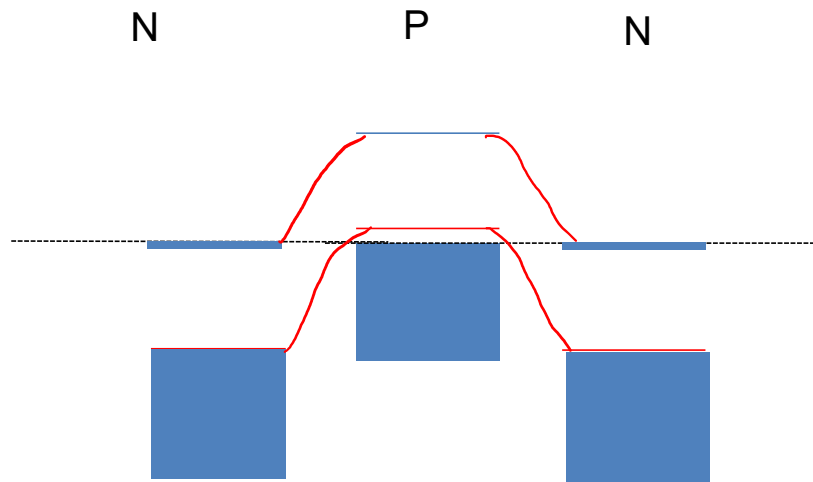
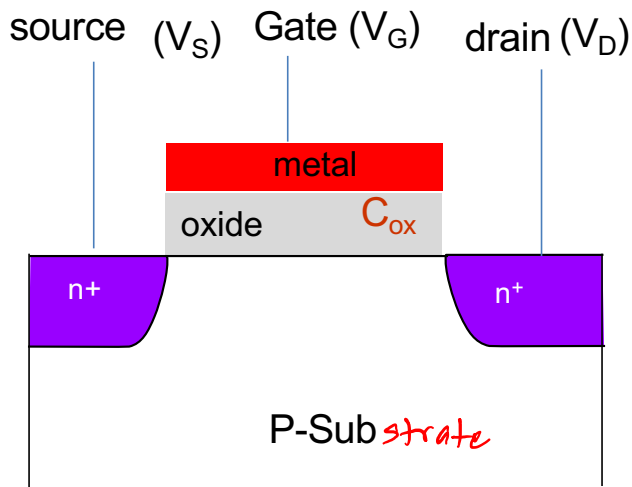
I-V of a PN junction Diode



P-n junction diode



Metal-Oxide-Semiconductor Field Effect Transistor (MOSFET)



- + or – in the name of n or p type material indicates extent of doping. N+ means doped **heavily** to n type.
- In common MOSFET source and drain voltages are interchangeable

P-type semiconductor in the middle with little to no electrons on the conduction band acts like an insulator

Recap: Capacitors (Review)

